

**Product Summary**

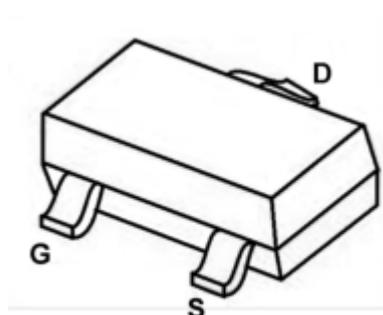
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
60V	2Ω@10V	0.22A
	2.5Ω@4.5V	

**Feature**

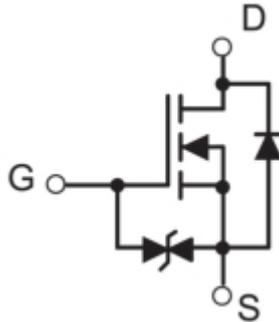
- We declare that the material of product compliance with RoHS requirements and Halogen Free
- Low threshold voltage,makes it ideal for low voltage applications
- ESD Protected

**Application**

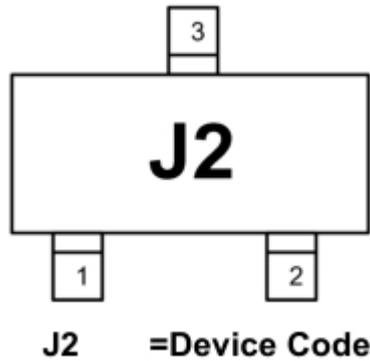
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

**Package**

**SOT-23**

### Circuit diagram



### Marking



### Absolute maximum ratings

( $T_a=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	0.22	A
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

## Electrical characteristics

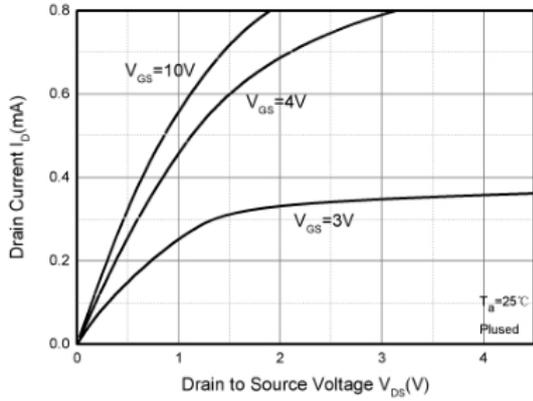
( $T_A=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 48V, V_{GS} = 0V$			1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 5$	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.7	1	1.45	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 500mA$		2	5	$\Omega$
		$V_{GS} = 4.5V, I_D = 200mA$		2.5	8	
<b>Dynamic characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1MHz$		27		$\mu F$
Output Capacitance	$C_{oss}$			13		
Reverse Transfer Capacitance	$C_{rss}$			6		
<b>Switching Characteristics</b>						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V, I_D = 0.29A,$ $V_{GS} = 10V, R_G = 6\Omega$			5	ns
Rise time	$t_r$				18	
Turn-off delay time	$t_{d(off)}$				36	
Fall time	$t_f$				14	
<b>Source-Drain Diode Characteristics</b>						
Diode Forward voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 500mA$	0.5		1.4	V

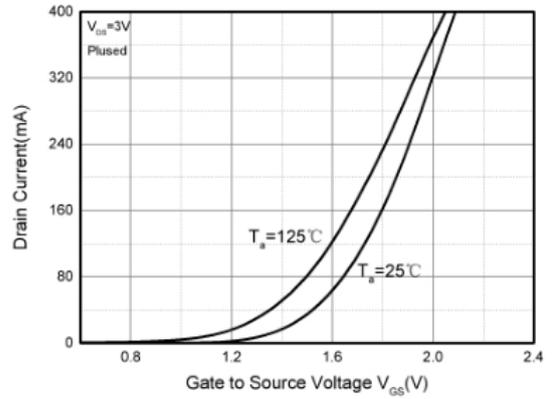
**Notes:**

1. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
2. These parameters have no way to verify.

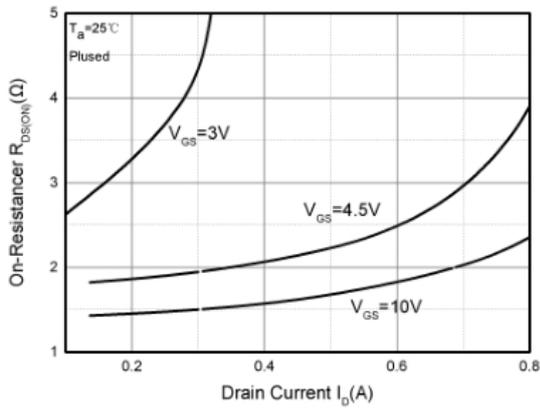
## Typical Characteristics



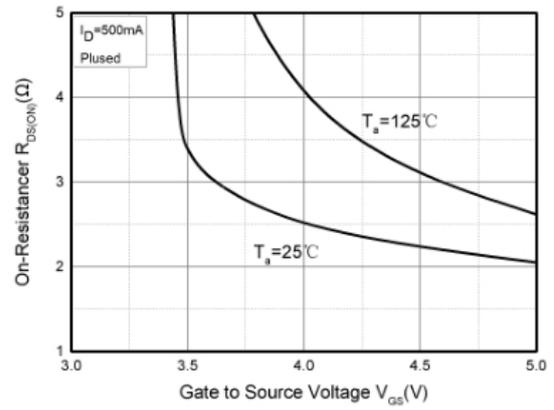
Output Characteristics



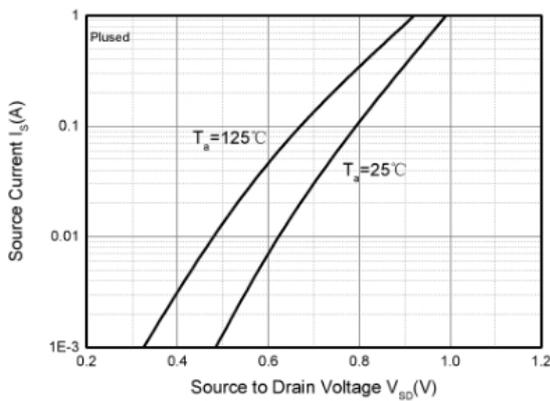
Transfer Characteristics



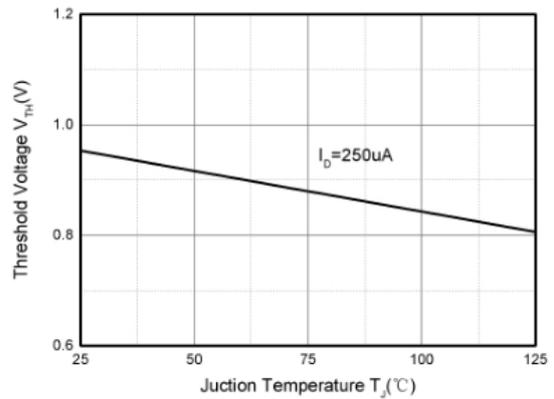
RDS(ON)— $I_D$



RDS(ON)— $V_{GS}$

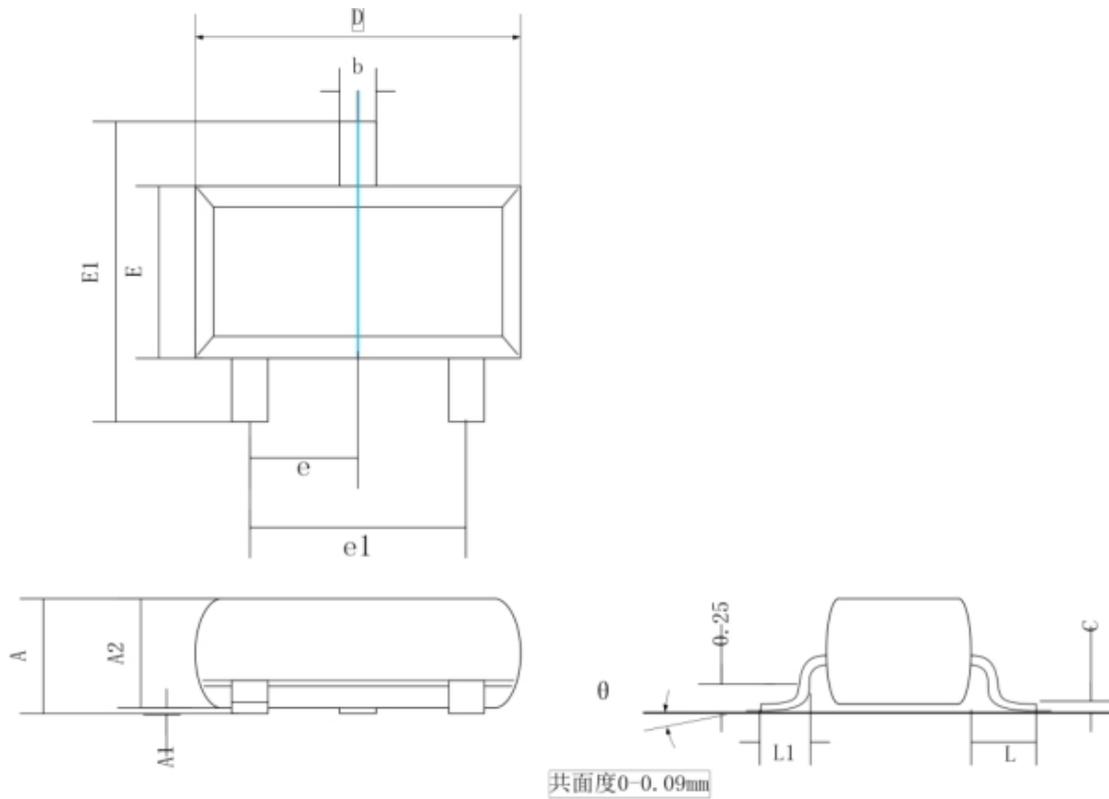


IS—VSD



Threshold Voltage

### SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
$\theta$	0°	8°